XPX4410XS

30V N-Channel Enhancement Mode Power MOSFET

RoHS COMPLIANT

Description

The XPX4410XS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

V_{DS} =30V,I_D =18A

$R_{DS(ON)}$=4.5mΩ (typ) @ V_{GS}=10V

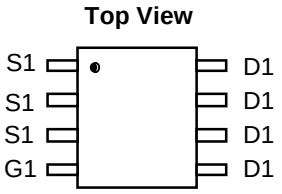
$R_{DS(ON)}$=6.0mΩ (typ) @ V_{GS}=4.5V

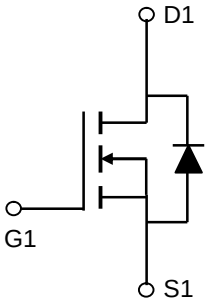
General Features

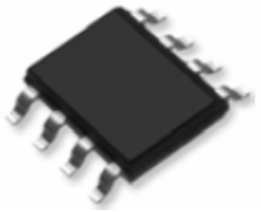
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply







Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
XPX4410XS	XPX4410XS	SOP-8	Ø330mm	12mm	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	18	A
Drain Current-Continuous(T_A=100℃)	I_D (100℃)	13.5	A
Pulsed Drain Current	I_{DM}	78	A
Maximum Power Dissipation	P_D	3.5	W
Single pulse avalanche energy (Note 5)	E_{AS}	220	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃
Thermal Resistance,Junction-to-Ambient(Note 2)	$R_{\theta JA}$	42	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	1.1	1.6	2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=10A	-	4.5	6.2	mΩ
		V_{GS}=4.5V, I_D=10A	-	6.0	7.0	
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=12A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=15V,V_{GS}=0V, F=1.0MHz	-	3819	-	PF
Output Capacitance	C_{oss}		-	350	-	PF
Reverse Transfer Capacitance	C_{rss}		-	240	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,I_D=10A V_{GS}=10V,R_{GEN}=2.7Ω	-	20	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	60	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=15V,I_D=10A, V_{GS}=10V	-	47.6	-	nC
Gate-Source Charge	Q_{gs}		-	4.9	-	nC
Gate-Drain Charge	Q_{gd}		-	10.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=10A	-	-	2.0	V
Diode Forward Current (Note 2)	I_S		-	-	18	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. E_{AS} condition: Tj=25℃,V_{DD}=15V,V_G=10V,L=0.5mH,Rg=25Ω

Typical Electrical and Thermal Characteristics (Curves)

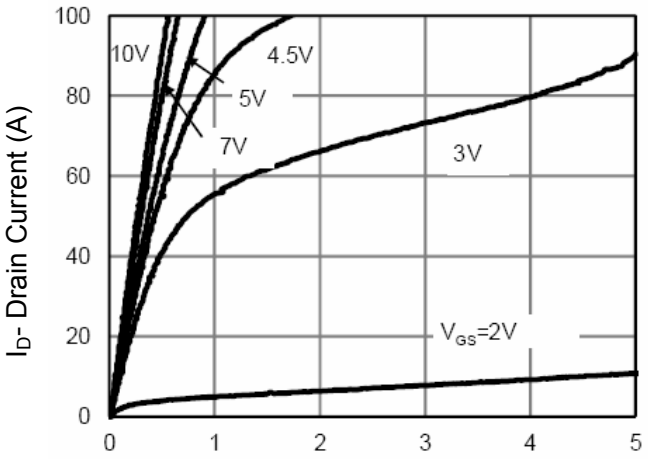


Figure 1 Output Characteristics

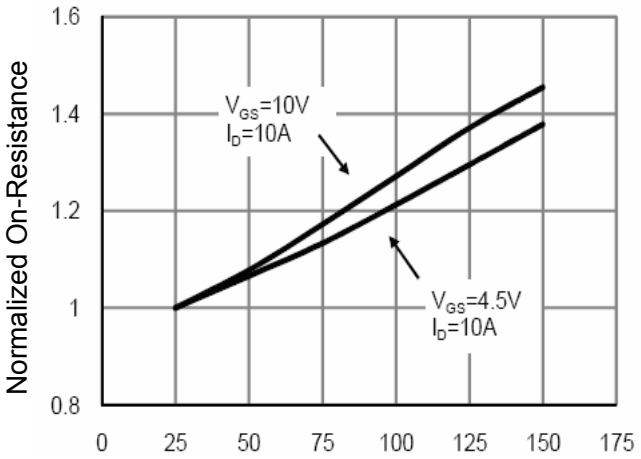


Figure 4 Rdson-Junction Temperature

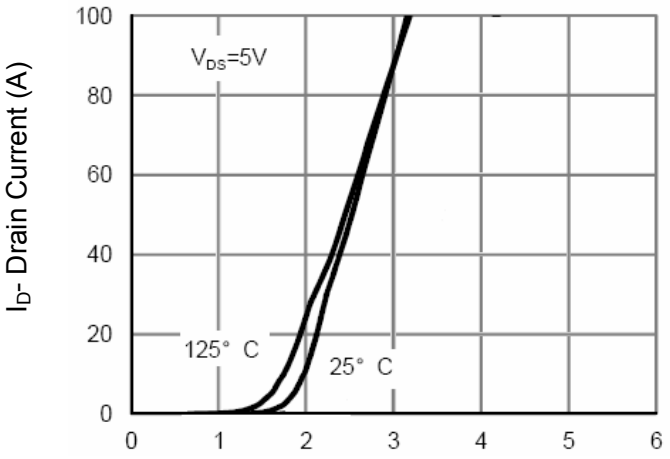


Figure 2 Transfer Characteristics

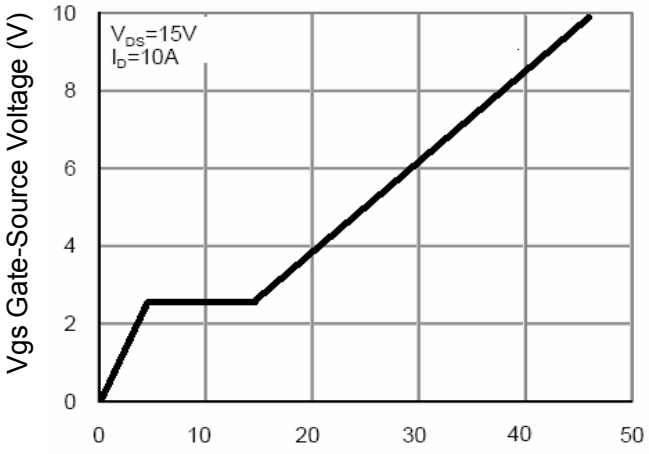


Figure 5 Gate Charge

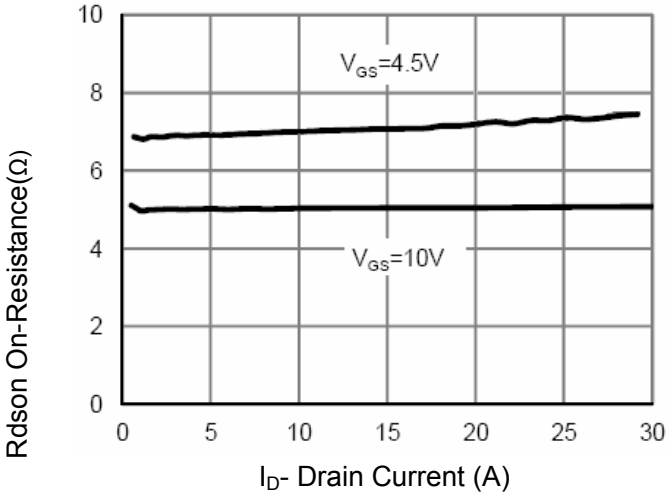


Figure 3 Rdson- Drain Current

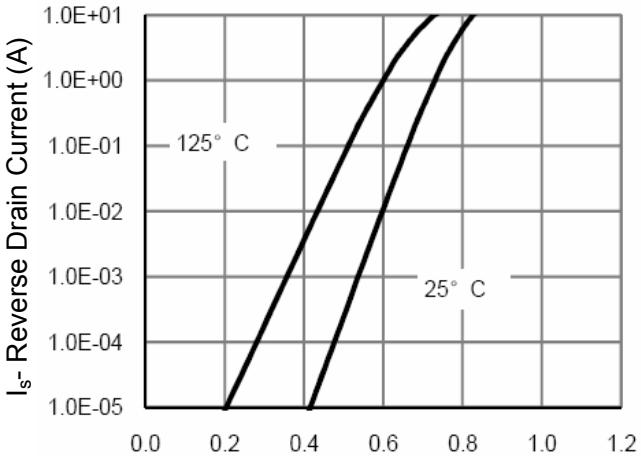


Figure 6 Source- Drain Diode Forward

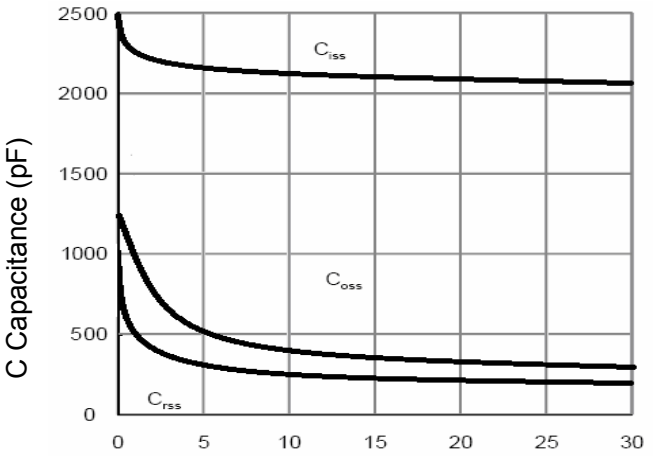
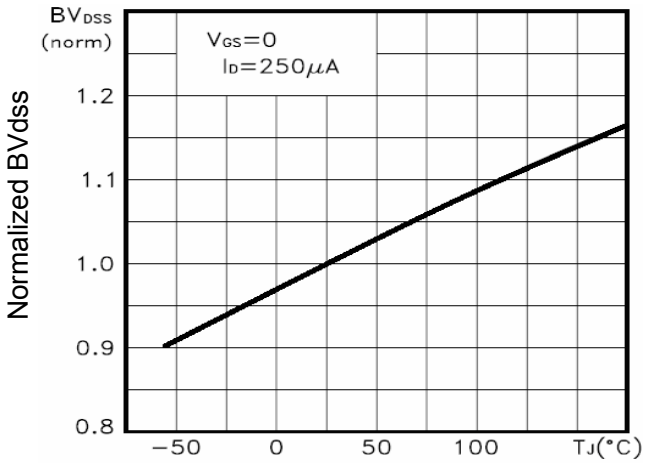


Figure 7 Capacitance vs Vds



TJ-Junction Temperature(℃)

Figure 9 BV_{DSS} vs Junction Temperature

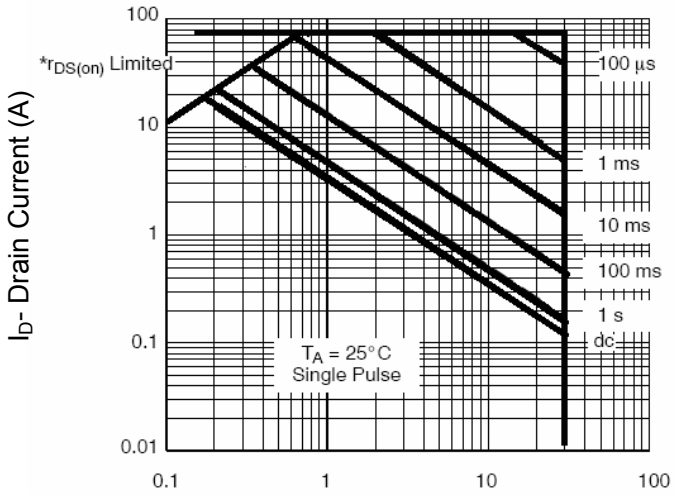
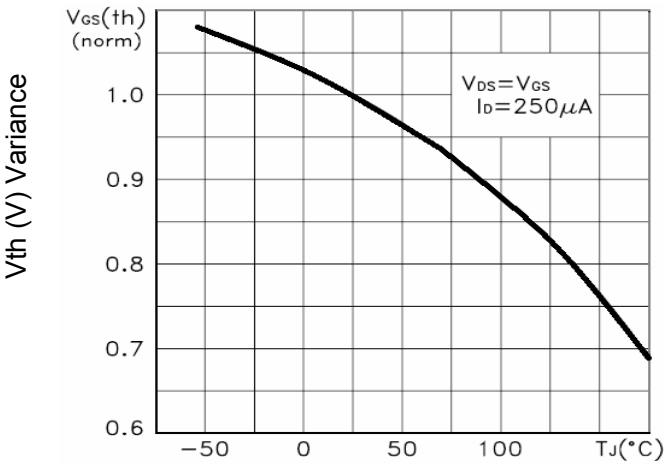


Figure 8 Safe Operation Area



TJ-Junction Temperature(℃)

Figure 10 $V_{GS(th)}$ vs Junction Temperature

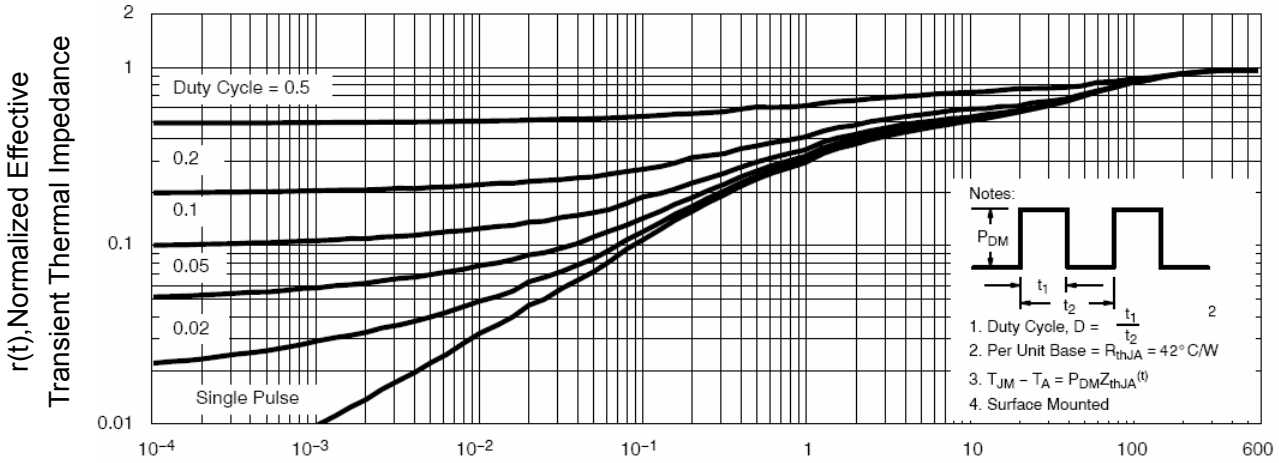
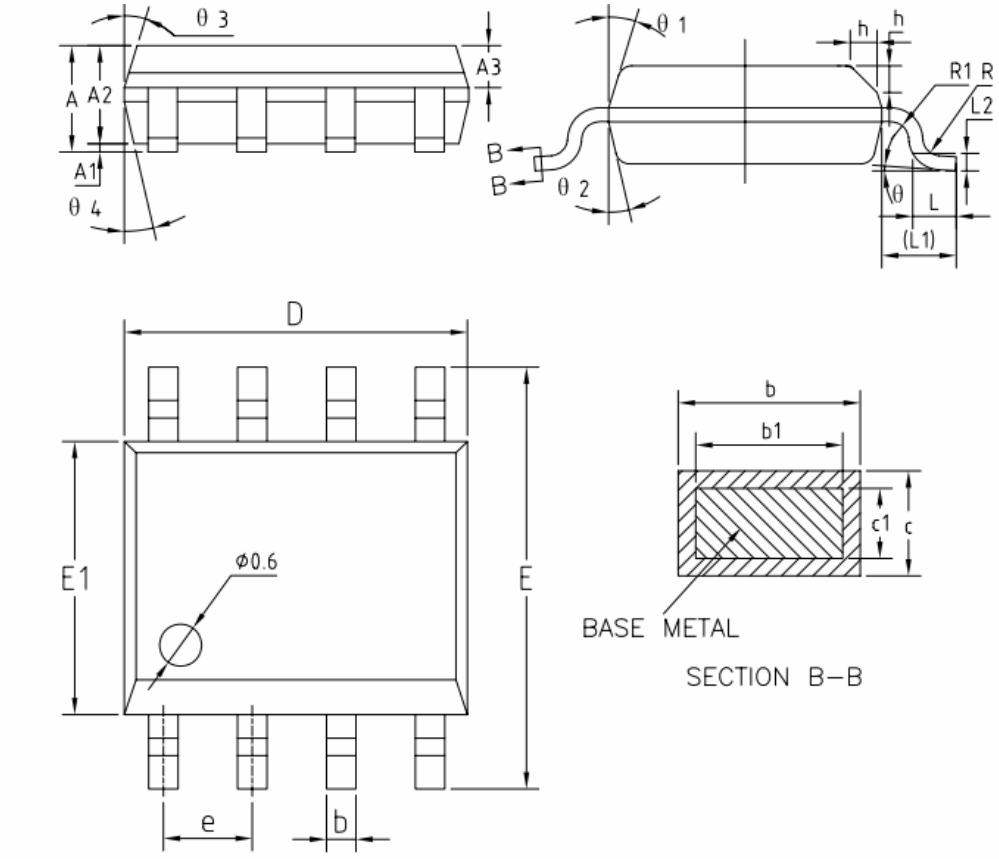


Figure 11 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	1.35	1.55	1.75
A1	0.10	0.15	0.25
A2	1.25	1.40	1.65
A3	0.50	0.60	0.70
b	0.38	–	0.51
b1	0.37	0.42	0.47
c	0.18	–	0.25
c1	0.17	0.20	0.23
D	4.80	4.90	5.00
E	5.80	6.00	6.20
E1	3.80	3.90	4.00
e	1.17	1.27	1.37
L	0.45	0.60	0.80
L1	1.04REF		
L2	0.25BSC		
R	0.07	–	–
R1	0.07	–	–
h	0.30	0.40	0.50
θ	0°	–	8°
θ 1	15°	17°	19°
θ 2	11°	13°	15°
θ 3	15°	17°	19°
θ 4	11°	13°	15°

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245℃±5℃	5sec±1sec
Pb-Free device	260℃+0/-5℃	5sec±1sec

This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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